

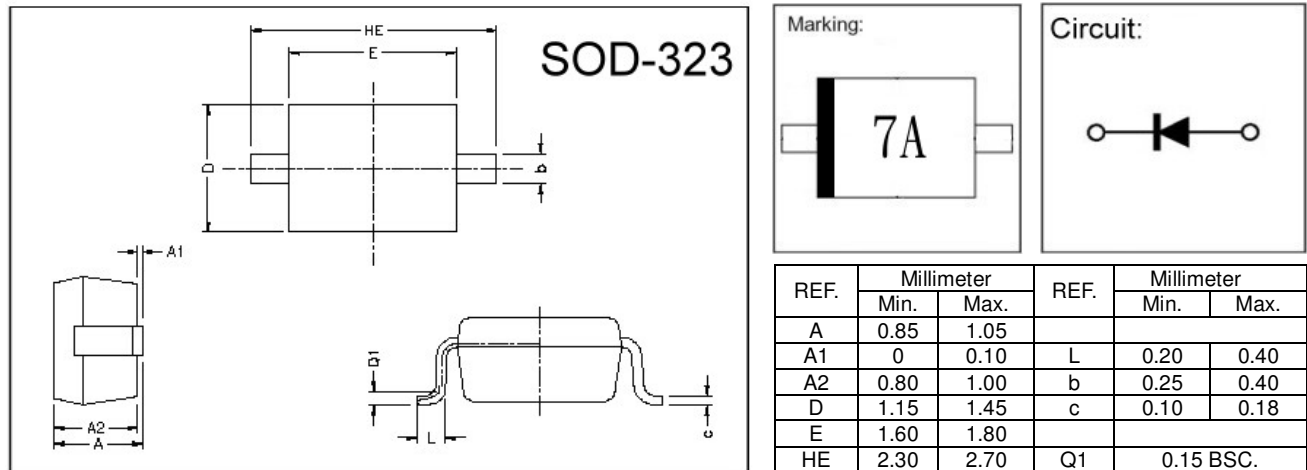
GD751SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.03A

Description

The GD751SD is designed for high speed switching for detection and high reliability.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RMS}	28	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	0.2	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	2.0	pF
Maximum Average Forward Rectified Current	I _o	0.03	A
Total Power Dissipation	PD	225	mW

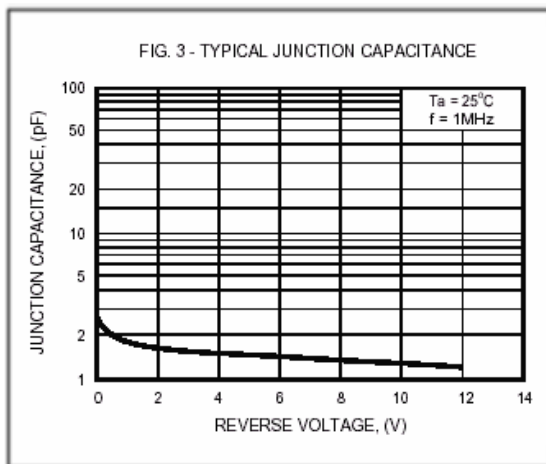
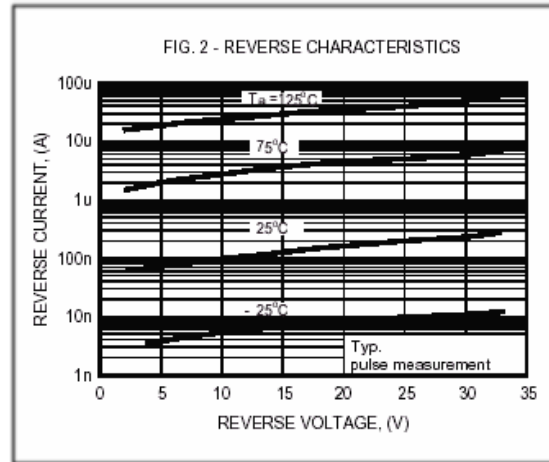
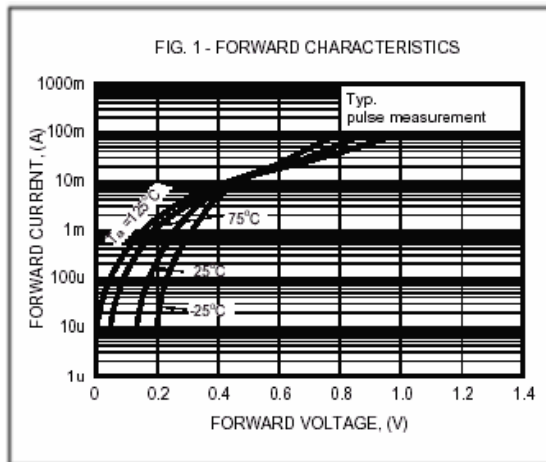
Characteristics at Ta = 25°C

Characteristics	Symbol	Max	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _F	0.37	V	I _F = 1mA
Maximum Average Reverse Current	I _R	0.5	uA	V _R = 30V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volt.

2. ESD sensitive product handling required.

Characteristics Curve



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